

AMENDMENTS TO THE SPECIFICATION:

Please cancel the originally-filed Abstract of the Disclosure and replace it with the following substitute Abstract of the Disclosure which appears as part of the Appendix.

Page 1, replace the paragraph beginning on line 15 with the following amended paragraph:

--A magnetic memory (Magnetic Random Access Memory: hereinafter, to be referred to as MARM MRAM) is known as one of memories for storing data in nonvolatile manner. A magnetic element used for the MRAM has a structure having a non-magnetic layer between ferromagnetic layers. The magnetic element shows a different resistance value in accordance with the fact that the magnetization vectors of the upper and lower ferromagnetic layers are parallel or anti-parallel. The different resistance value can be related to "1" or "0". By detecting the resistance value of the magnetic element, it is possible to read the data written in the magnetic element.--